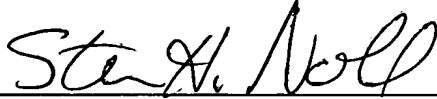


Early examination on the merits is respectfully requested.

Respectfully submitted,



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Final
Drawing
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JCS

BOX PCT

IN THE UNITED STATES DESIGNATED/ELECTED OFFICE
OF THE UNITED STATES PATENT AND TRADEMARK OFFICE
UNDER THE PATENT COOPERATION TREATY-CHAPTER II

5 **REQUEST FOR APPROVAL OF DRAWING CHANGES**

APPLICANT(S): Thomas Aeugle et al.
ATTORNEY DOCKET NO.: P99,1696
INTERNATIONAL APPLICATION NO.: PCT/EP98/01405
INTERNATIONAL FILING DATE: 11 March 1998
INVENTION: "METHOD FOR THE PRODUCTION OF A VERTICAL MOS
TRANSISTOR"

Assistant Commissioner for Patents
Washington, D.C. 20231

S I R:

Applicants herewith request approval of the drawing changes in Figures 1, 2
and 13 as shown on the drawing copies marked in red attached hereto.

Submitted by,

Steven H. Noll (Reg. 28,982)

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FIG 1

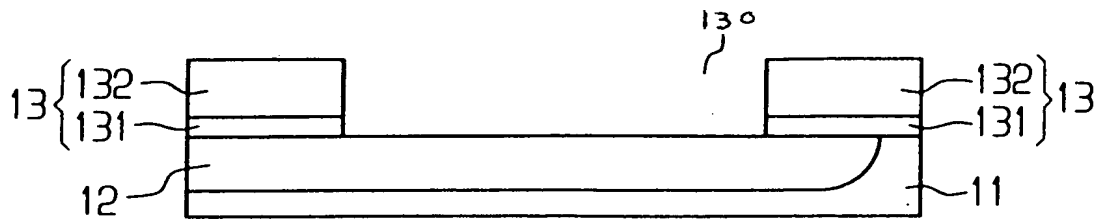


FIG 2

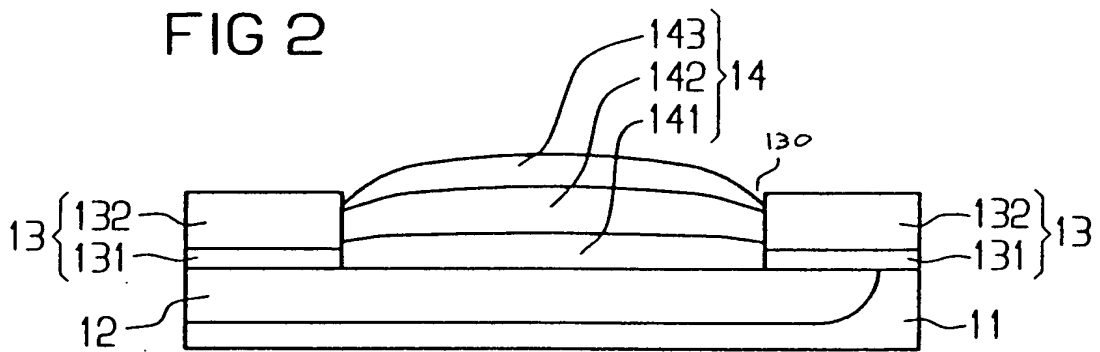
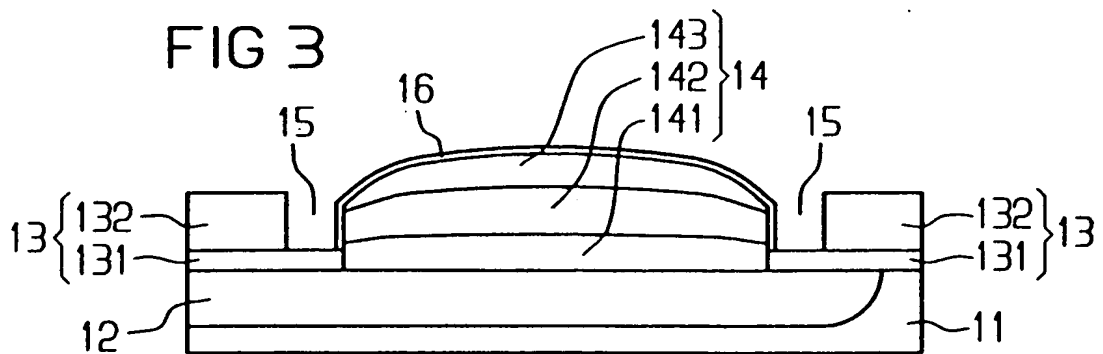


FIG 3



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FIG 13

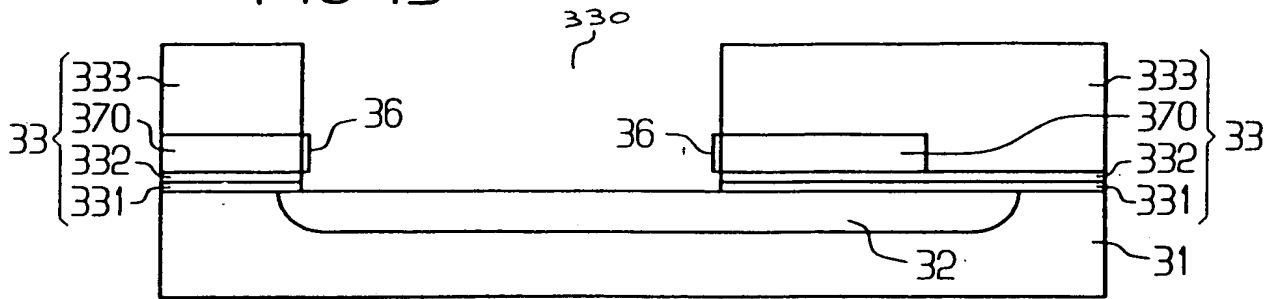


FIG 14

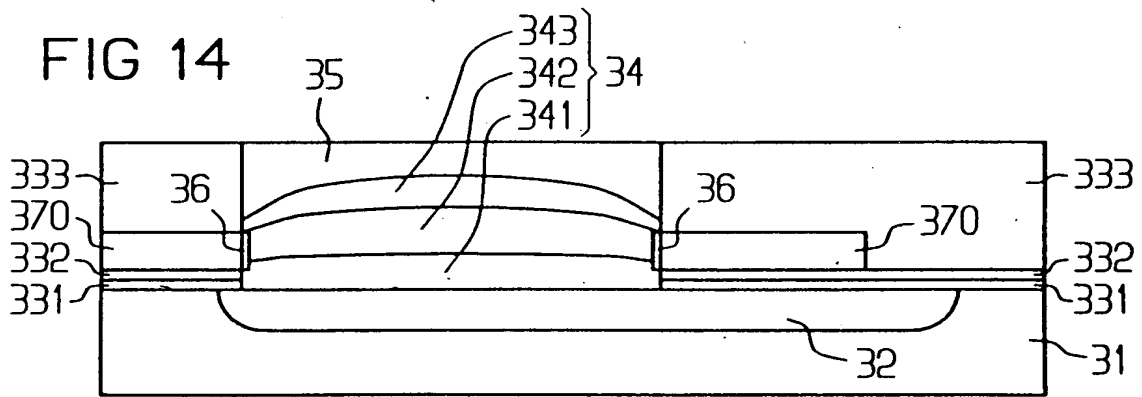
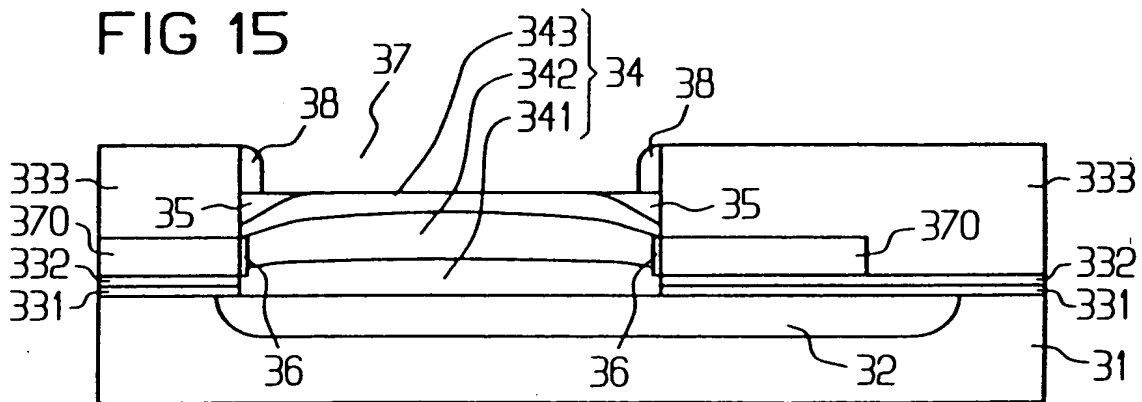


FIG 15



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